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Kind regards,

Team Nexperia

PHP101NQ03LT

N-channel TrenchMOS logic level FET

Rev. 04 — 2 March 2009

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Simple gate drive required due to low gate charge
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC converters

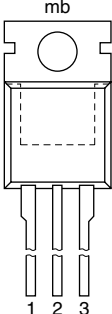
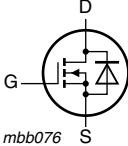
1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	30	V
I_D	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see Figure 1 ; see Figure 3	-	-	75	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ see Figure 2	-	-	166	W
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 5\text{ V}; I_D = 50\text{ A};$ $V_{DS} = 15\text{ V}; T_j = 25\text{ °C};$ see Figure 11	-	8	-	nC
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $T_j = 25\text{ °C};$ see Figure 9 ; see Figure 10	-	4.5	5.5	mΩ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT78
(TO-220AB; SC-46)

3. Ordering information

Table 3. Ordering information

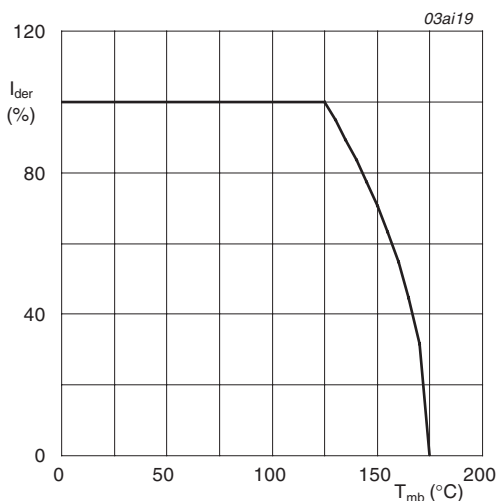
Type number	Package		Version
	Name	Description	
PHP101NQ03LT	TO-220AB; SC-46	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

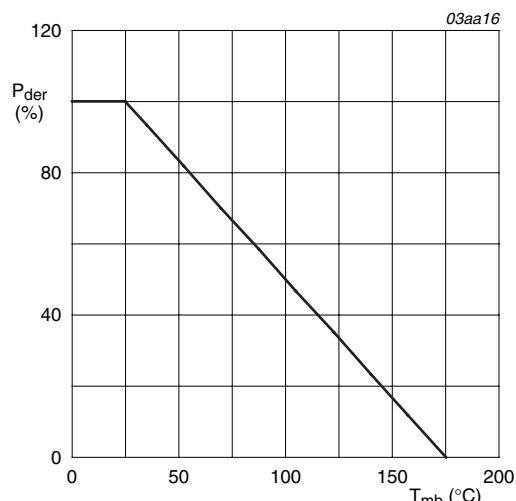
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see Figure 1	-	75	A
		V _{GS} = 10 V; T _{mb} = 25 °C; see Figure 1 ; see Figure 3	-	75	A
I _{DM}	peak drain current	t _p ≤ 10 μs; pulsed; T _{mb} = 25 °C; see Figure 3	-	240	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	166	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
V _{GSM}	peak gate-source voltage	pulsed; δ = 25 %; t _p ≤ 50 μs; T _j ≤ 150 °C	-25	25	V
Source-drain diode					
I _S	source current	T _{mb} = 25 °C	-	75	A
I _{SM}	peak source current	t _p ≤ 10 μs; pulsed; T _{mb} = 25 °C	-	240	A
Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(initial)} = 25 °C; I _D = 43 A; V _{sup} ≤ 15 V; unclamped; t _p = 0.19 ms; R _{GS} = 50 Ω	-	185	mJ



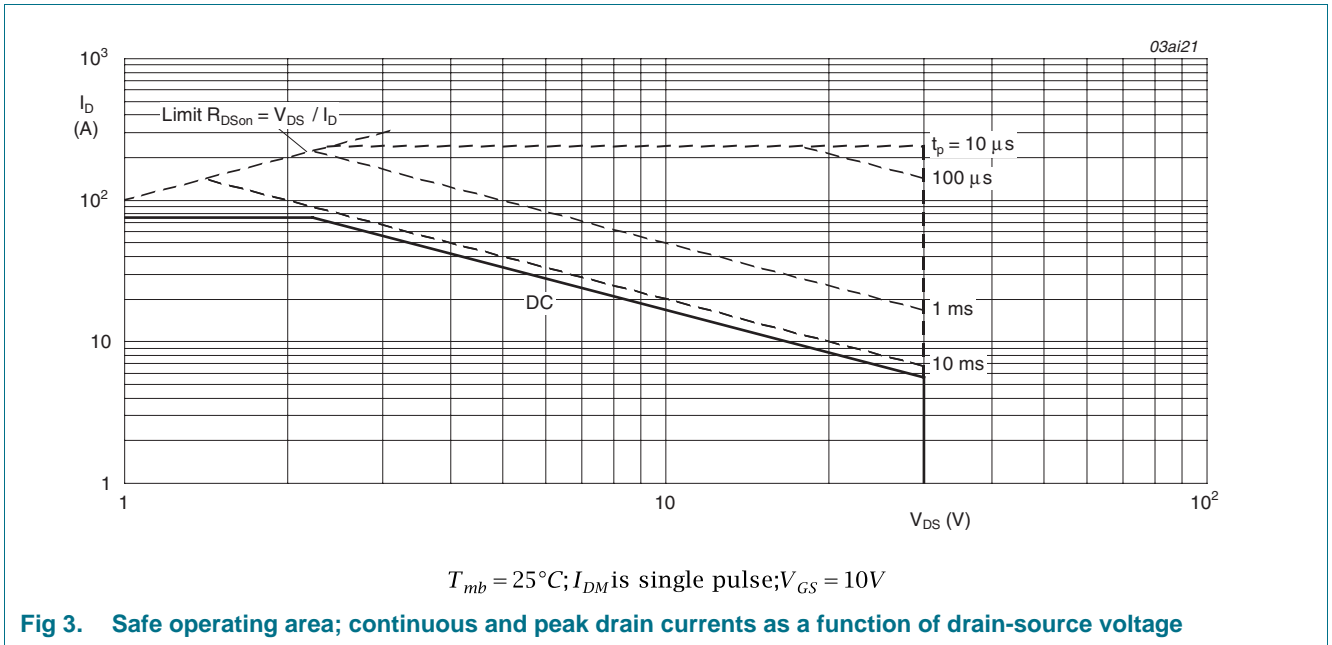
$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.19	K/W

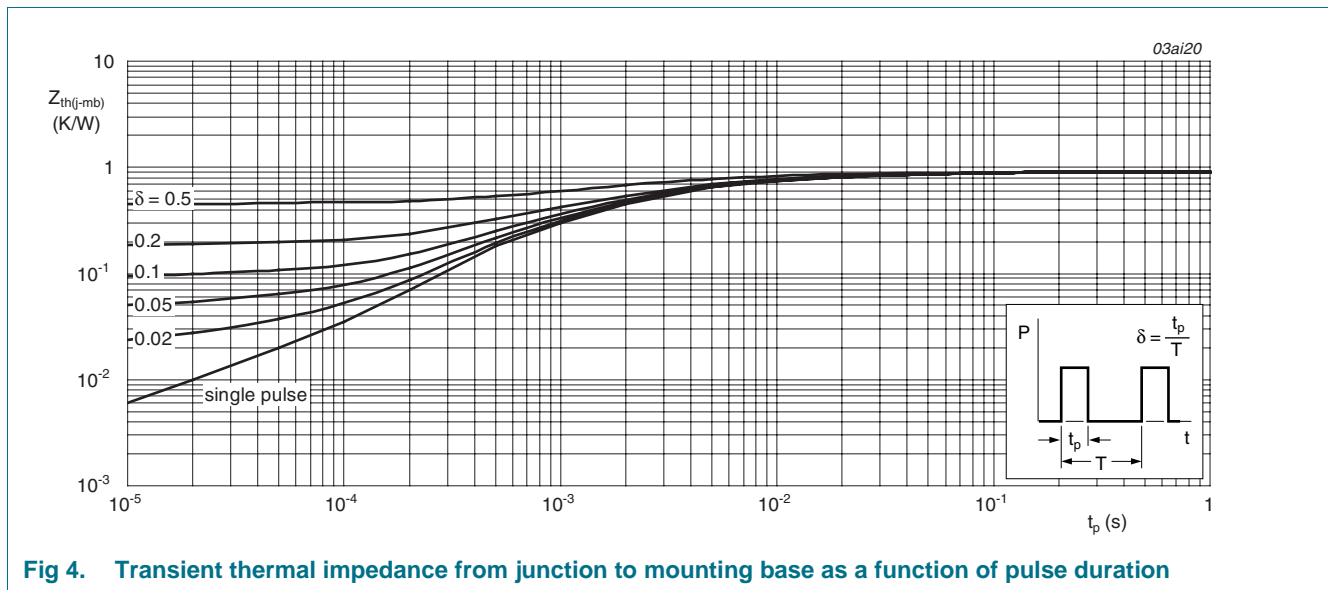
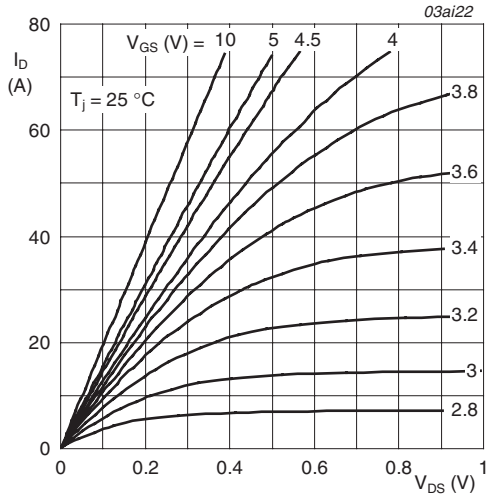


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

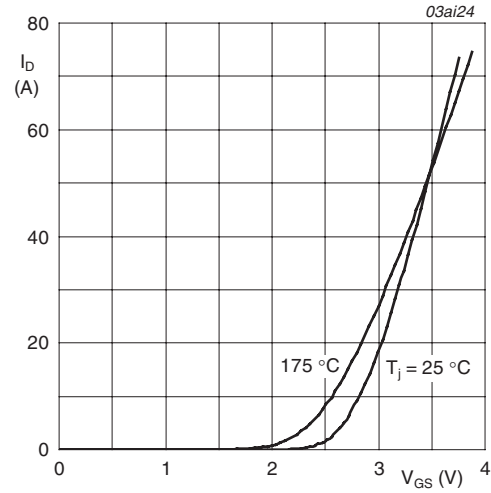
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	27	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$; see Figure 7 ; see Figure 8	-	-	2.9	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C$; see Figure 7 ; see Figure 8	0.6	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$; see Figure 7 ; see Figure 8	1	1.9	2.5	V
I_{DSS}	drain leakage current	$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.05	1	μA
		$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	10	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 25 A; T_j = 25 \text{ }^\circ C$; see Figure 9 ; see Figure 10	-	4.5	5.5	m Ω
		$V_{GS} = 5 V; I_D = 25 A; T_j = 175 \text{ }^\circ C$; see Figure 9 ; see Figure 10	-	10.5	13.5	m Ω
		$V_{GS} = 5 V; I_D = 25 A; T_j = 25 \text{ }^\circ C$; see Figure 9 ; see Figure 10	-	5.8	7.5	m Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 50 A; V_{DS} = 15 V; V_{GS} = 5 V; T_j = 25 \text{ }^\circ C$; see Figure 11	-	23	-	nC
Q_{GS}	gate-source charge		-	10.5	-	nC
Q_{GD}	gate-drain charge		-	8	-	nC
C_{iss}	input capacitance	$V_{DS} = 25 V; V_{GS} = 0 V; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$; see Figure 12	-	2180	-	pF
C_{oss}	output capacitance		-	600	-	pF
C_{rss}	reverse transfer capacitance		-	225	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 V; R_L = 0.6 \Omega; V_{GS} = 4.5 V; R_{G(ext)} = 5.6 \Omega; T_j = 25 \text{ }^\circ C; I_D = 25 A$	-	23	-	ns
t_r	rise time		-	90	-	ns
$t_{d(off)}$	turn-off delay time		-	37	-	ns
t_f	fall time		-	33	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$; see Figure 13	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 10 A; dI_S/dt = -100 A/\mu s; V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 \text{ }^\circ C$	-	37	-	ns
Q_r	recovered charge		-	33	-	nC



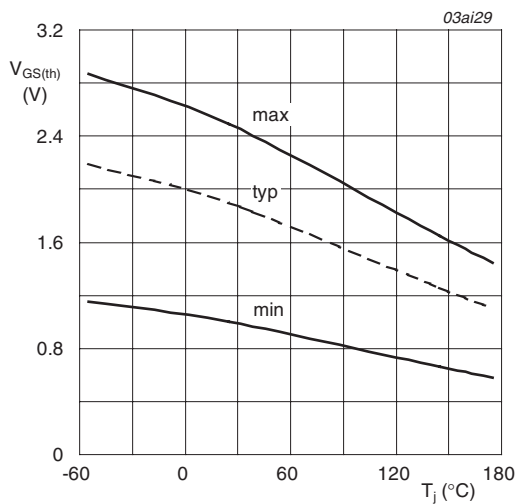
$T_j = 25^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



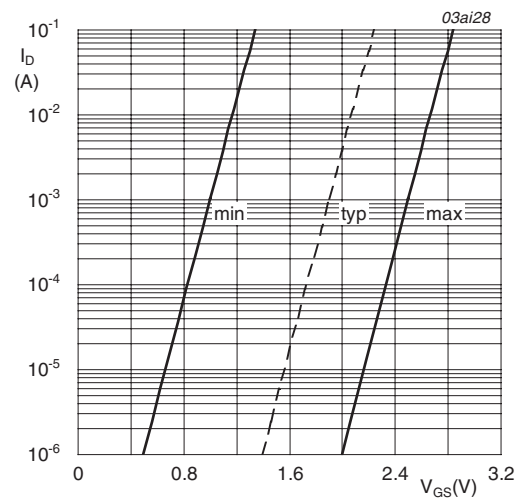
$T_j = 25^\circ\text{C}$ and $175^\circ\text{C}; V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



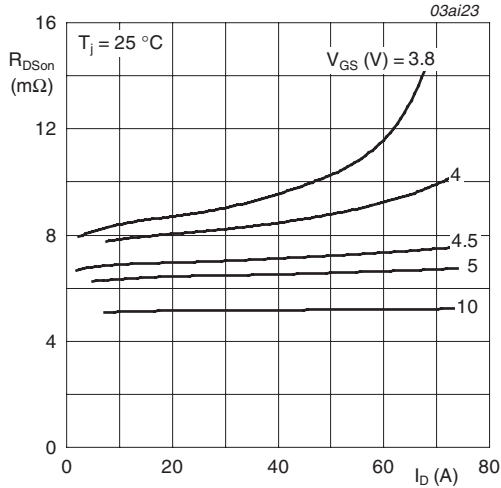
$I_D = 1\text{mA}; V_{DS} = V_{GS}$

Fig 7. Gate-source threshold voltage as a function of junction temperature



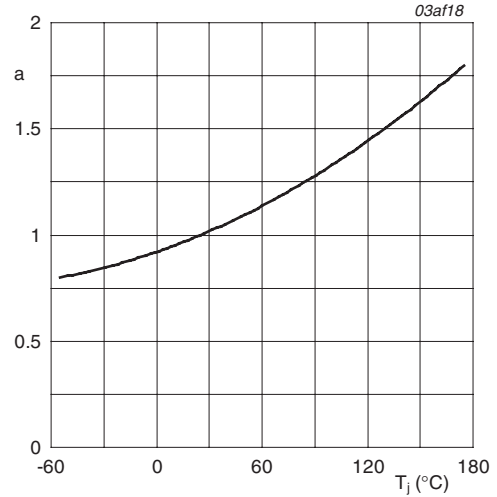
$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

Fig 8. Sub-threshold drain current as a function of gate-source voltage



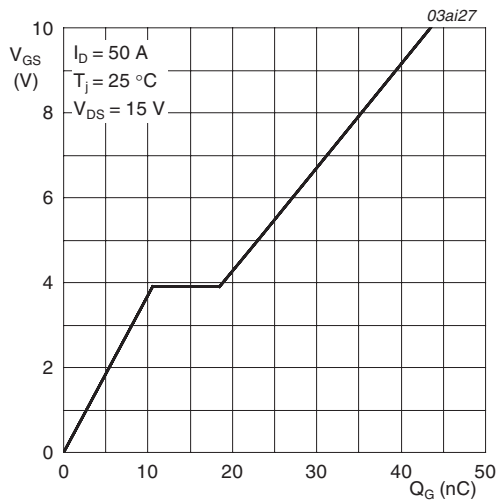
$T_j = 25^\circ\text{C}$

Fig 9. Drain-source on-state resistance as a function of drain current; typical values



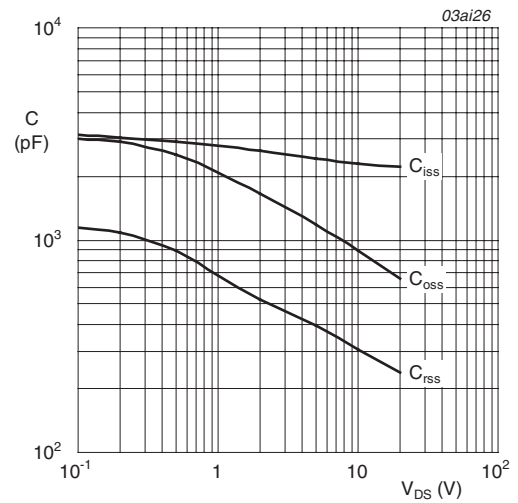
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



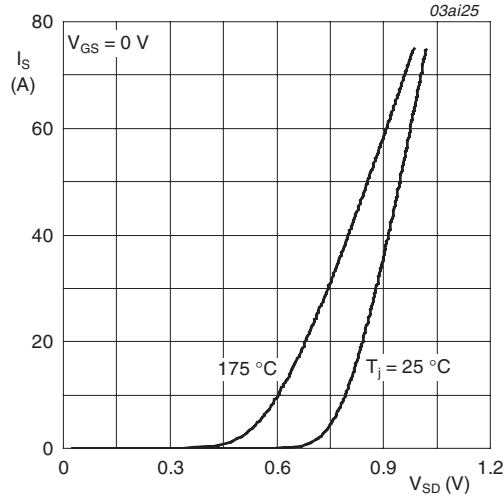
$I_D = 50\text{ A}; V_{DS} = 15\text{ V}$

Fig 11. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$T_j = 25\text{ °C}$ and $175\text{ °C}; V_{GS} = 0\text{ V}$

Fig 13. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

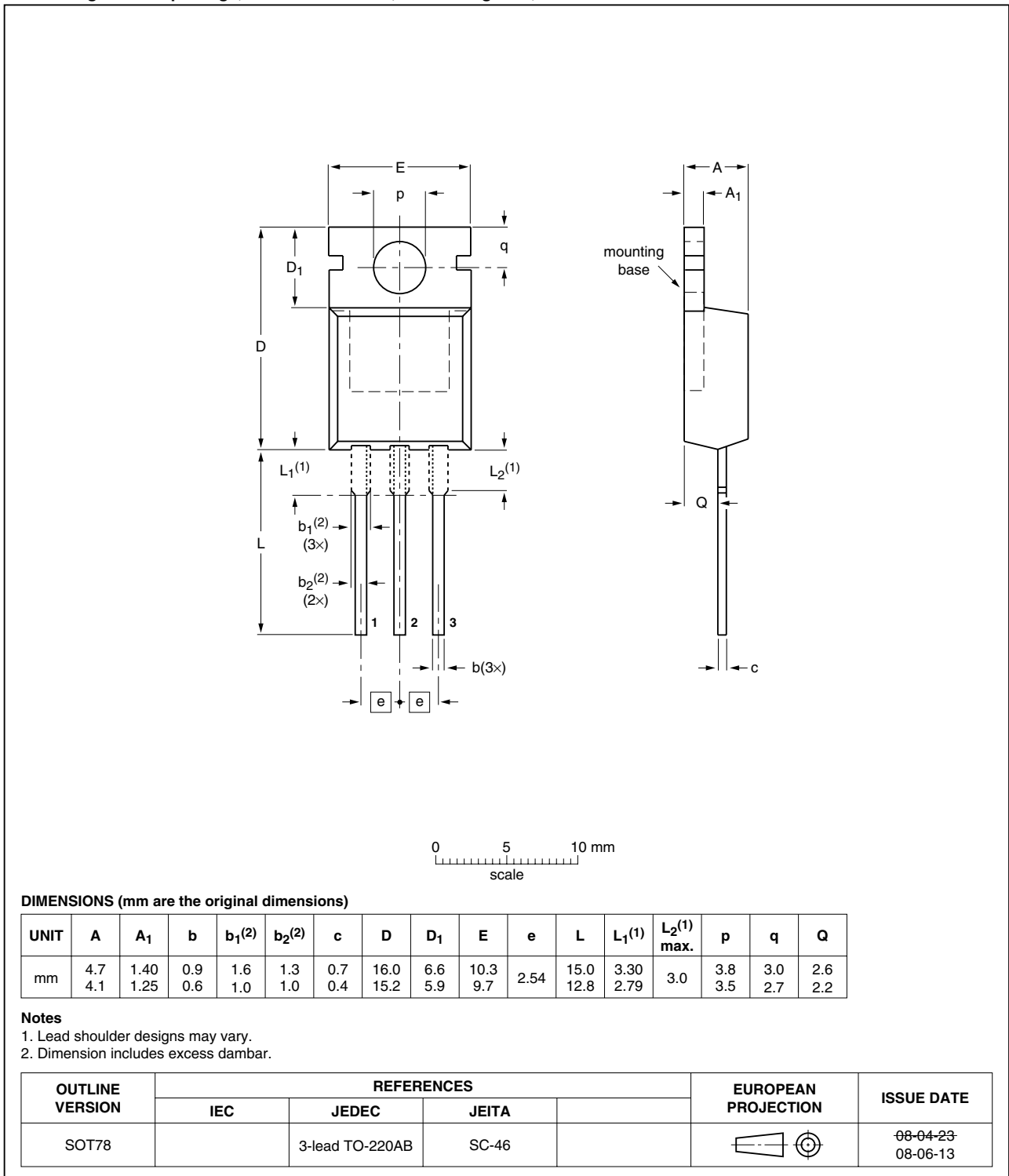


Fig 14. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP101NQ03LT_4	20090302	Product data sheet	-	PHP_PHU101NQ03LT_3
Modifications:				
			<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. 	
PHP_PHU101NQ03LT_3	20051117	Product data sheet	CPCN # 200309016	PHP_PHU101NQ03LT-02
PHP_PHU101NQ03LT-02 (9397 750 10927)	20030225	Product data	-	PHP_PHD_PHB_PHU101 NQ03LT-01
PHP_PHD_PHB_PHU101 NQ03LT-01 (9397 750 09307)	20020220	Product data	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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